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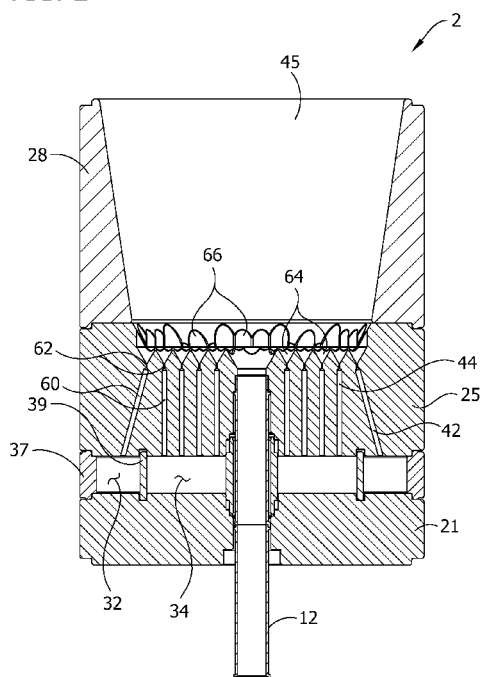
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(54) Title: FLUIDIZED BED REACTOR SYSTEMS AND METHODS FOR REDUCING THE DEPOSITION OF SILICON ON REACTOR WALLS

FIG. 2



(57) Abstract: Gas distribution units of fluidized bed reactors are configured to direct thermally decomposable compounds to the center portion of the reactor and away from the reactor wall to prevent deposition of material on the reactor wall and process for producing polycrystalline silicon product in a reactor that reduce the amount of silicon which deposits on the reactor wall.



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